## . 10/572730 IAP20RecdPCT/PTO 21 MAR 2006

VIA Express Mail EV786328877US

Docket Number
40404.30/tt

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Hiroshi OJI	International Application No.: PCT/JP2005/11260
Serial No.: Currently unknown	
Filing or 371(c) Date: Concurrently herewith	International Filing Date:
Title: SEMICONDUCTOR DEVICE HAVING HIGH-K GATE DIELECTRIC LAYER AND METHOD FOR MANUFACTURING THE SAME	June 20, 2005

## **PRELIMINARY AMENDMENT**

Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Prior to examination on the merits of the above-identified patent application,
Applicant respectfully requests entry and consideration of the following Amendment:

	Amendments to the Specification begin on page 2 of this paper.	
	Amendments to the Drawings begin on page of this paper and incluan attached replacement sheet.	ude
	Listing of the Claims begins on page 5. No amendments have been material to the Claims.	ad€
	Remarks/Arguments begin on page 8 of this paper.	
	Please note, if a box is not checked, then no corresponding amendment is beir	ng
ade.		